



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SMPS MOSFET

IRF7455

HEXFET® Power MOSFET

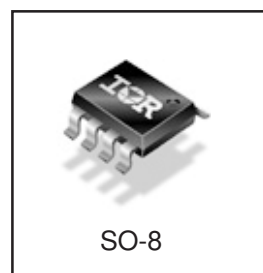
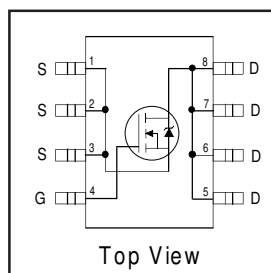
Applications

- High Frequency DC-DC Converters with Synchronous Rectification

V_{DS}	$R_{DS(on)}$ max	I_D
30V	0.0075Ω	15A

Benefits

- Ultra-Low $R_{DS(on)}$ at 4.5V V_{GS}
- Low Charge and Low Gate Impedance to Reduce Switching Losses
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 12	V
I_D @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	15	A
I_D @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	12	
I_{DM}	Pulsed Drain Current①	120	
P_D @ $T_A = 25^\circ\text{C}$	Maximum Power Dissipation③	2.5	W
P_D @ $T_A = 70^\circ\text{C}$	Maximum Power Dissipation③	1.6	W
	Linear Derating Factor	0.02	W/°C
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient④	50	°C/W

Typical SMPS Topologies

- Telecom 48V Input Converters with Logic-Level Driven Synchronous Rectifiers

Notes ① through ④ are on page 8
www.irf.com

IRF7455

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V$, $I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.0060	0.0075	Ω	$V_{GS} = 10V$, $I_D = 15A$ ④
		—	0.0069	0.009		$V_{GS} = 4.5V$, $I_D = 12A$ ④
		—	0.010	0.020		$V_{GS} = 2.8V$, $I_D = 3.5A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	0.6	—	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 24V$, $V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V$, $V_{GS} = 0V$, $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -12V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	44	—	—	S	$V_{DS} = 10V$, $I_D = 15A$
Q_g	Total Gate Charge	—	37	56	nC	$I_D = 15A$
Q_{gs}	Gate-to-Source Charge	—	8.9	13		$V_{DS} = 24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	13	20		$V_{GS} = 5.0V$, ③
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = 15V$
t_r	Rise Time	—	18	—		$I_D = 1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	51	—		$R_G = 6.0\Omega$
t_f	Fall Time	—	44	—		$V_{GS} = 4.5V$ ③
C_{iss}	Input Capacitance	—	3480	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	870	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	100	—		$f = 1.0\text{MHz}$

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	200	mJ
I_{AR}	Avalanche Current①	—	15	A
E_{AR}	Repetitive Avalanche Energy①	—	0.25	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	120		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}$, $I_S = 2.5A$, $V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	64	96	ns	$T_J = 25^\circ\text{C}$, $I_F = 2.5A$
Q_{rr}	Reverse Recovery Charge	—	99	150	nC	$di/dt = 100A/\mu s$ ③

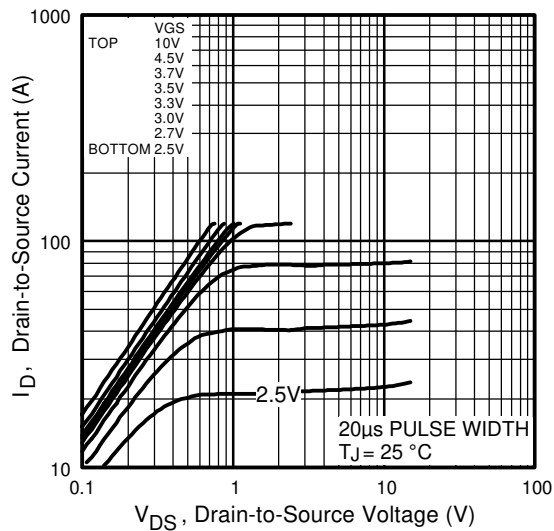


Fig 1. Typical Output Characteristics

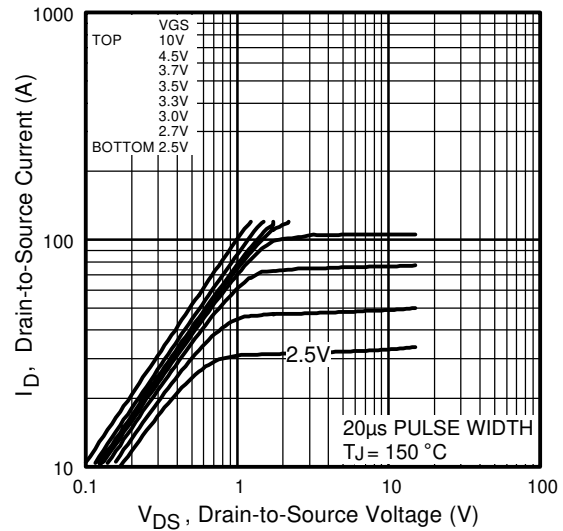


Fig 2. Typical Output Characteristics

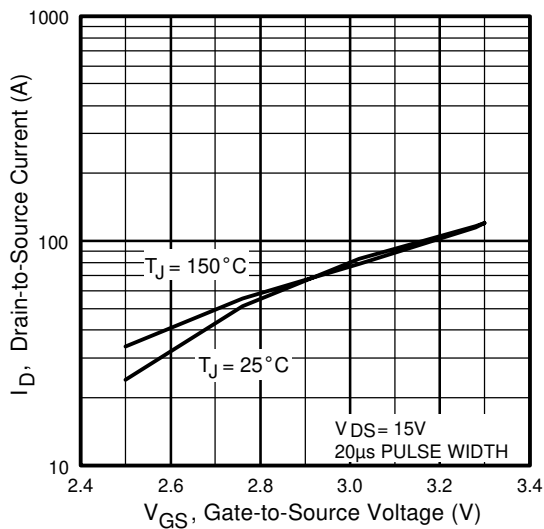


Fig 3. Typical Transfer Characteristics

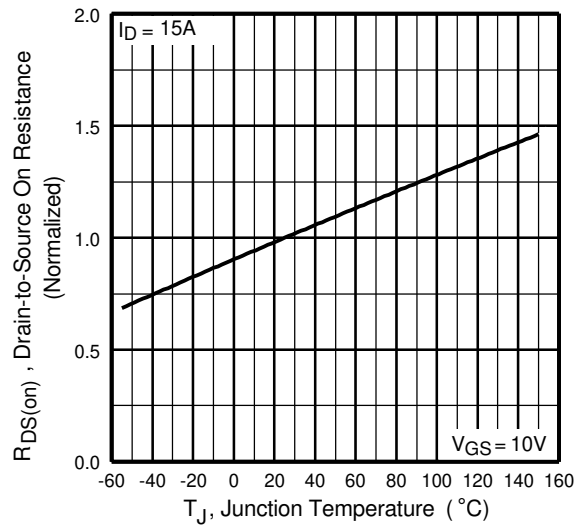


Fig 4. Normalized On-Resistance
Vs. Temperature

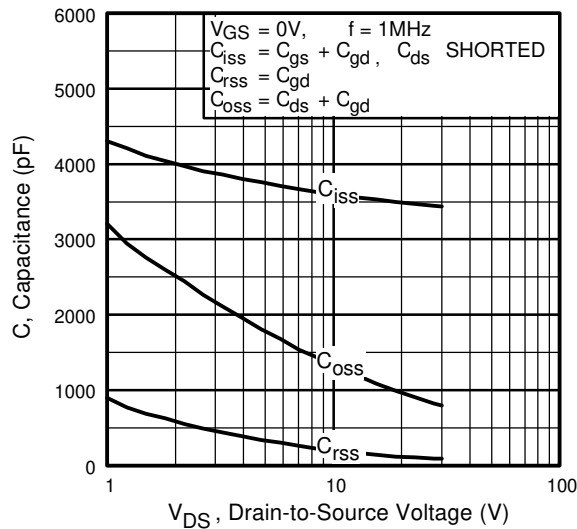


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

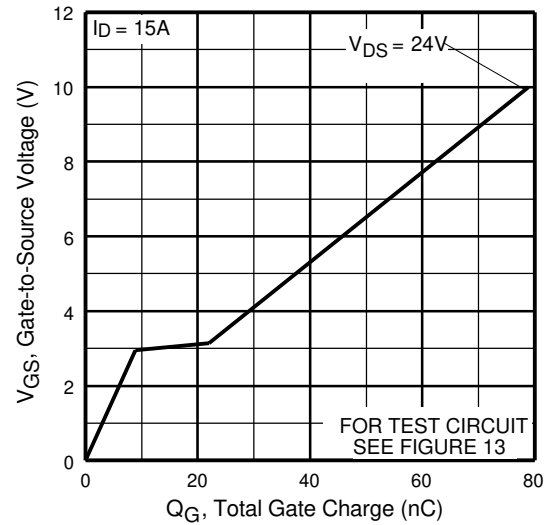


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

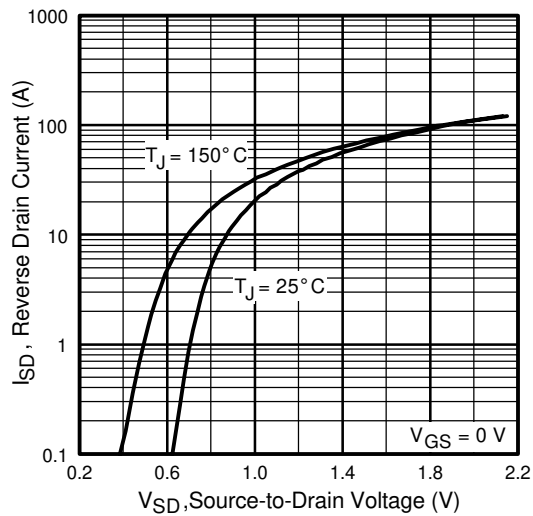


Fig 7. Typical Source-Drain Diode Forward Voltage

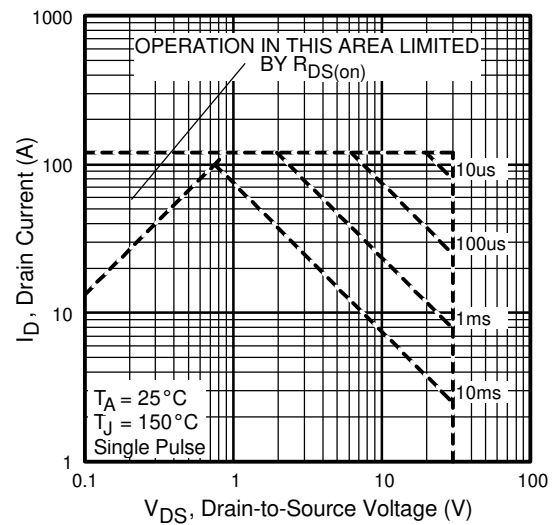


Fig 8. Maximum Safe Operating Area

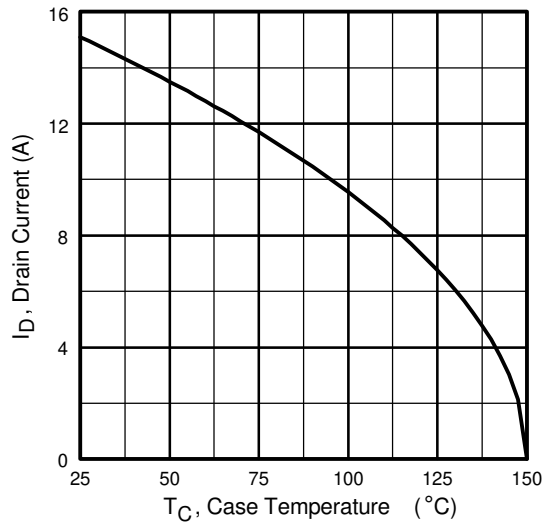


Fig 9. Maximum Drain Current Vs. Case Temperature

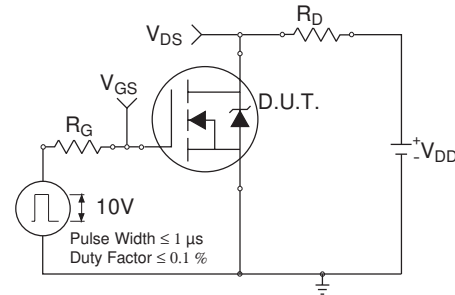


Fig 10a. Switching Time Test Circuit

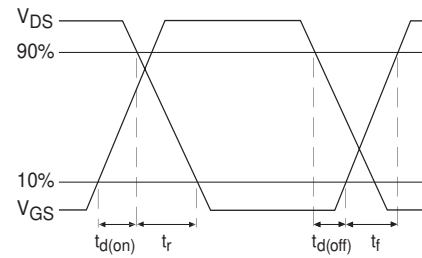


Fig 10b. Switching Time Waveforms

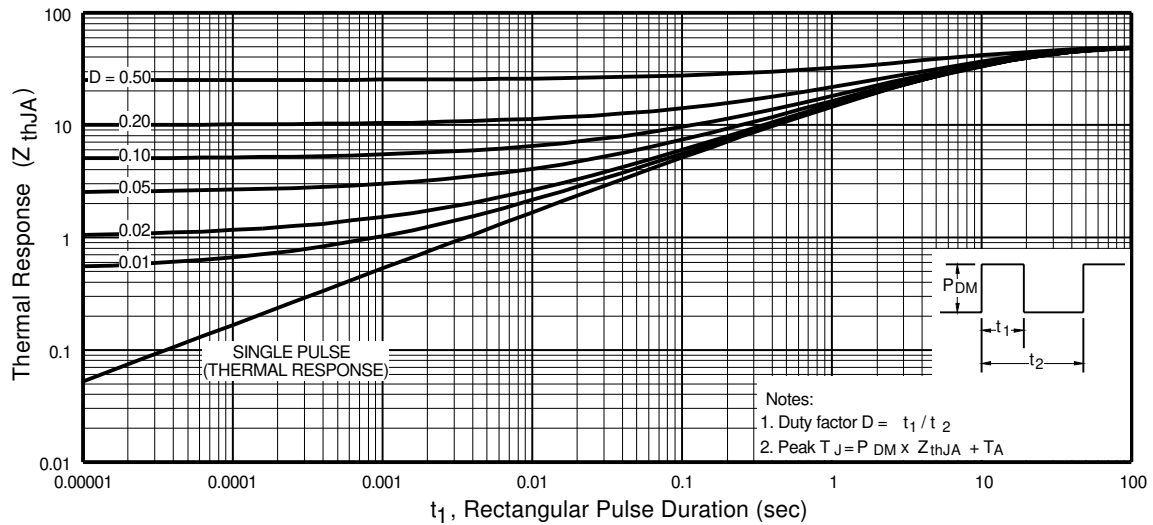


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

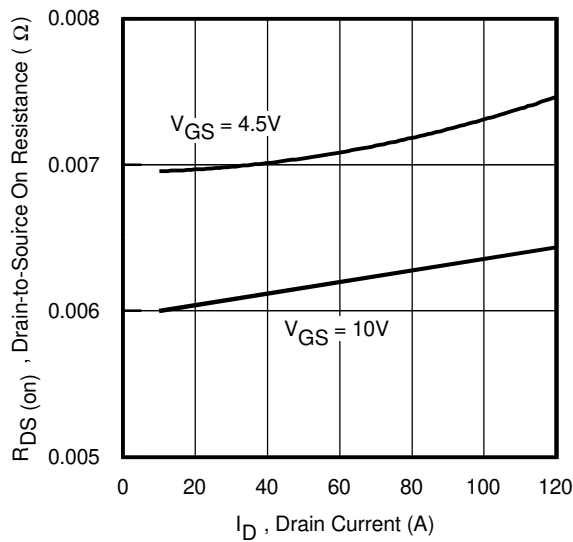


Fig 12. On-Resistance Vs. Drain Current

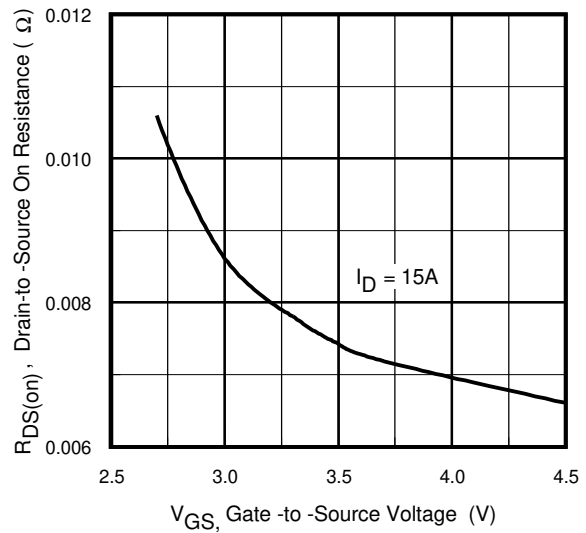


Fig 13. On-Resistance Vs. Gate Voltage

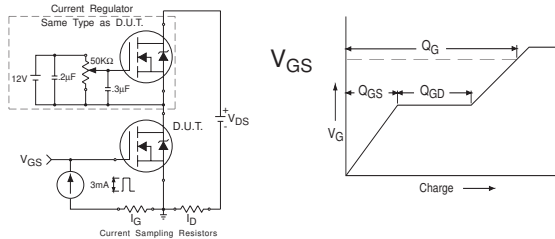


Fig 13a&b. Basic Gate Charge Test Circuit and Waveform

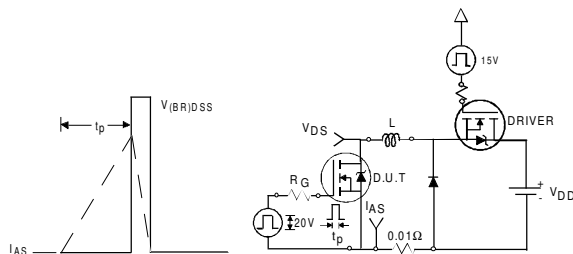


Fig 14a&b. Unclamped Inductive Test circuit and Waveforms

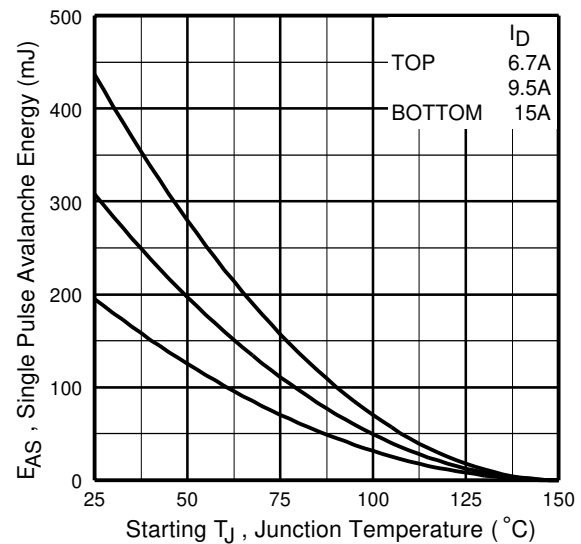
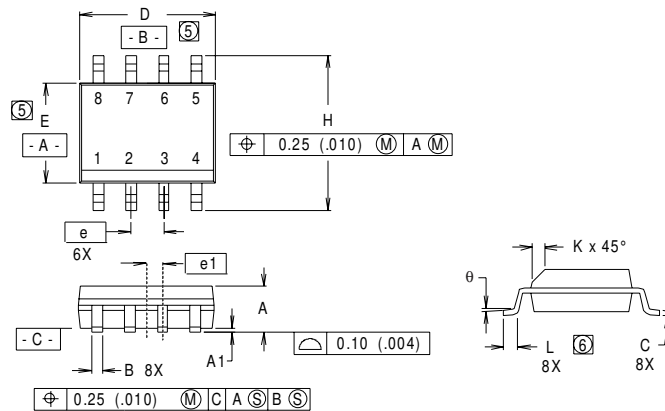


Fig 14c. Maximum Avalanche Energy Vs. Drain Current

SO-8 Package Details

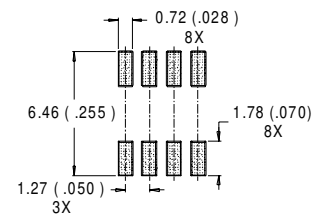


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
- ⑥ DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

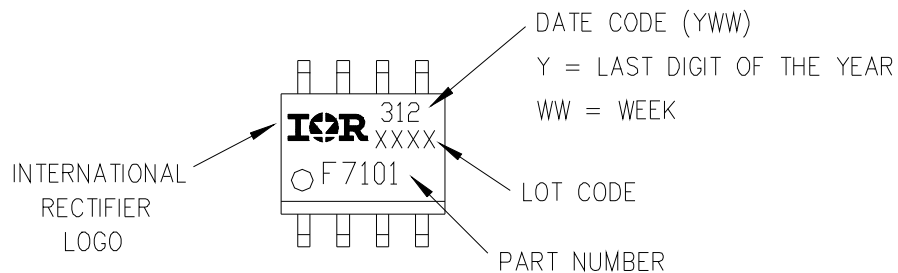
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
θ	0°	8°	0°	8°

RECOMMENDED FOOTPRINT



SO-8 Part Marking

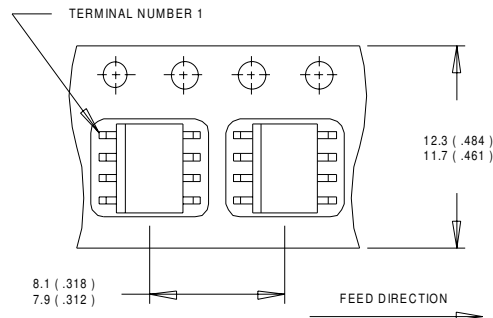
EXAMPLE: THIS IS AN IRF7101



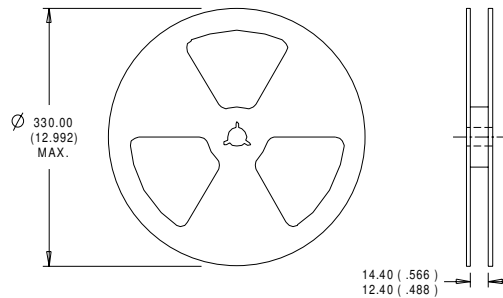
IRF7455

International
IR Rectifier

SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.8\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 15\text{A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t < 10$ sec

International
IR Rectifier

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IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590
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Data and specifications subject to change without notice. 4/00

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